

STRUCTURE TYPE

Silicon Monolithic Integrated Circuit

Step down 1ch DC/DC converter Controller for Lap top PC

PRODUCT SERIES FEATURES

BD95513MUV Built in H³REG DC/DC controller

- Switching Frequency Variable (f=200kHz~600kHz)
- Built in N-MOS FET (typ:120mΩ)

○ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Limit	Unit
Input Voltage 1	Vcc	7 *1	V
Input Voltage 2	VDD	7 *1	V
Input Voltage 3	AVIN	30 *1	V
Input Voltage 4	Vin	30 *1	٧
EXTVCC Voltage	EXTVcc	7 *1	V
BOOT Voltage	BOOT	35	V
BOOT-SW Voltage	BOOT-SW	7 *1	V
Output Feedback Voltage	FB	VCC	V
SS / FS / MODE Voltage	SS/FS/MODE	VCC	V
VREG Voltage	VREG	VCC	V
EN/CTL Input Voltage	EN/CTL	7 *1	٧
PGOOD Voltage	PGOOD	7 *1	V
Output Current (Average)	Isw	3 *1	Α
Power Dissipation 1	Pd1	0.38*2	W
Power Dissipation 2	Pd2	0.88*3*6	W
Power Dissipation 3	Pd3	2.06*4*6	W
Power Dissipation 4	Pd4	4.56*5*6	W
Operating Temperature Range	Topr	-10~+100	°
Storage Temperature Range	Tstg	-55~+150	°C
Maximum Junction Temperature	Tjmax	· +150	°

^{*1} Not to exceed Pd, ASO, and Tjmax=150°C.

OPERATING CONDITIONS (Ta=25°C)

Parameter	Symbol	MIN	MAX	Unit
Input Voltage 1	Vcc	4.5	5.5	V
Input Voltage 2	VDD	4.5	5.5	V
Input Voltage 3	AVin	4.5	28	V
Input Voltage 4	Vin	4.5	28	V
EXTVCC Voltage	EXTVcc	4.5	5.5	V
BOOT Voltage	BOOT	4.5	33	V
SW Voltage	SW	-0.7	28	V
BOOT-SW Voltage	BOOT-SW	4.5	5.5	V
MODE Input Voltage	MODE	0	5.5	V
EN/CTL Input Voltage	EN/CTL	0	5.5	V
PGOOD Voltage	PGOOD	0	5.5	V
Minimum ON Time	tonmin	-	100	nsec

[★] This product is not designed for protection against radioactive rays.

Status of this document

^{*2} Reduced by 3.0mW for each increase in Ta of 1°C over 25°C (when don't mounted on a heat radiation board)

² Reduced by 7.0mW for increase in Ta of 1°C over 25°C. (when mounted on a board 70.0mm×70mm×1.6mm Glass-epoxy PCB which has 1 layer. (Copper foil area: 0mm²))

4 Reduced by 16.5mW for increase in Ta of 1°C over 25°C. (when mounted on a board 70.0mm×70mm×1.6mm Glass-epoxy PCB which has 4 layers. (1⁴ and 4⁵° copper foil area: 20.2mm², 2°d and 3°d copper foil area: 5505mm²))

5 Reduced by 36.5mW for increase in Ta of 1°C over 25°C. (when mounted on a board 70.0mm×70mm×1.6mm Glass-epoxy PCB which has 4 layers. (1⁴ and 4⁵° copper foil area: 25.0.2mm², 2°d and 3°d copper foil area: 5505mm²))

which has 4 layers. (All copper foil area : 5505mm²))

*6 It is the value when reverse side is soldered. Incase not soldered, power dissipation is decreased.

The Japanese version of this document is the official specification.

This translated version is intended only as a reference, to aid in understanding the official version.

If there are any differences between the original and translated versions of this document, the official Japanese language version takes priority.

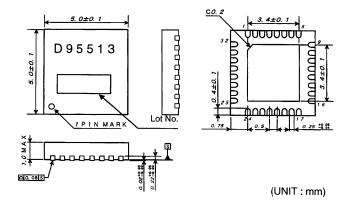


 $\bigcirc \underline{\mathsf{ELECTRICAL}\ \mathsf{CHARACTERISTICS}\ (\mathsf{unless}\ \mathsf{otherwise}\ \mathsf{noted},\ \mathsf{Ta} = 25^{\circ}\!\!\mathsf{C}\ \ \mathsf{AVIN} = 12\mathsf{V},\ \mathsf{VCC} = \mathsf{VDD} = \mathsf{VREG},\ \mathsf{EN/CTL} = 5\mathsf{V},\ \mathsf{MODE} = 0\mathsf{V},\ \mathsf{RFS} = 180\mathsf{k}\ \Omega)}$

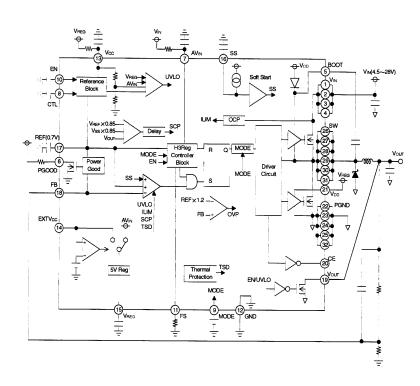
ELECTRICAL CHARACTERISTICS (L			Standard Value			
Parameter	Symbol	MIN	TYP	MAX	Unit	Condition
[Whole Device block]						
AVIN bias current 1	lin1	-	1200	1800	μΑ	
AVIN bias current 2	lin2	-	150	250	μΑ	EXTVcc=5V
AVIN standby current	linstb	-	0	10	μΑ	CTL=EN=0V
EN Low voltage	ENlow	GND	-	0.8	V	
EN High voltage	ENhigh	2.3	-	5.5	V	
EN bias current	İEN	-	12	20	μΑ	
CTL Low voltage	CTLlow	GND	-	0.8	V	
CTL High voltage	CTLhigh	2.3	-	5.5	V	
CTL bias current	ICTL	-	1	6	μΑ	
[5V Linear regulator block]						
VREG output voltage	VREG	4.90	5.00	5.10	V	AVIN=6.0 to 25V
Maximum current	IREG	200		-	mA	
[5V switch block]	<u> </u>					
EXTVcc input threshold voltage	EVcc_uvlo	4.2	4.4	4.6	V	EXTVcc:Sweep up
Switch resistance	Revcc	<u>-</u>	1.0	2.0	Ω	
[Under Voltage Locked Out block]					,	T
AVIN threshold voltage	AVIN_UVLO	4.1	4.3	4.5	V	Vcc:Sweep up
AVIN hysteresis voltage	dAVIN_UVLO	100	160	220	mV	Vcc:Sweep down
VREG threshold voltage	VREG_UVLO	4.1	4.3	4.5	V	VREG:Sweep up
VREG hysteresis voltage	dVREG_UVLO	100	160	220	mV_	VREG:Sweep down
[H ³ REG [™] block]						
ON Time	ton	400	500	600	nsec	
MAX ON Time	tonmax	10.0	22.0	35.0	μsec	
MIN OFF Time	toffmin	-	450	550	nsec	
[FET Driver block]						
High side ON resistance	Ron_high	-	120	200	mΩ	
Low side ON resistance	Ron_low	-	120	200	mΩ	
[SCP block]					т	T
SCP startup voltage	Vscp	0.420	0.490	0.560	V	@VFB:30%down
Delay time	tscp	0.5	1	2	ms	
[OVP block]						
OVP setting voltage	Vovp	0.800	0.840	0.880	V	@VFB:20%up
[Soft start block]	_			L	1	·
Charge current	Iss	1.4	2.2	3.0	μΑ	
Standby voltage	Vss_stb	-		100	mV	
	V 55_5ID	_		100	1111	<u> </u>
[Current Limit block]	r					
Output current control	ІОСР	3	-	•	A	
[Output Voltage Sense block]			0 700		T	1
Feedback pin voltage 1	VFB1	0.693	0.700	0.707	V	Ta=-10°C to 100°C
Feedback pin voltage 2	VFB2	0.690	0.700	0.710	V	lout=0A to 2A
Feedback pin bias current	IFB	-100	0	100	nA_	L
[Mode block]	Г				_	Ta
SLLM	VthsLLM	VCC-0.5	-	VCC	V	SLLM (Maximum LG offtime:∞)
Forced continuous mode	Vthcont	GND	-	0.5	V	Continuos mode
Open voltage	VMODE	1.5	-	3.0	V	
[Power Good block]						
VFB Power Good Low voltage	VFB PL	0.605	0.630	0.655	V	@VFB:10%down
VFB Power Good High voltage	VFB PH	0.745	0.770	0.795	V	@Vгв:10%up



OPHYSICAL DIMENSIONS



OBlock diagram



○Pin No. Pin name

PIN	PIN name	
No.	1 II Tianio	
1	Vin	
2	VIN	
3	Vin	
4	Vin	
5	воот	
6	PGOOD	
7	AVIN	
8	CTL	
9	MODE	
10	EN	
11	FS	
12	GND	
13	Vcc	
14	EXTVcc	
15	VREG	
16	SS	
17	REF	
18	FB	
19	Vout	
20	CE	
21	VDD	
22	PGND	
23	PGND	
24	PGND	
25	PGND	
26	SW	
27	SW	
28	SW	
29	SW	
30	SW	
31	SW	
32	PGND	

REV. A



ONOTES FOR USE

1. Absolute maximum ratings

An excess in the absolute maximum ratings, such as supply voltage, temperature range of operating conditions, etc., can break down the devices, thus making impossible to identify breaking mode, such as a short circuit or an open circuit. If any over rated values will expect to exceed the absolute maximum ratings, consider adding circuit protection devices, such as fuses.

2. GND voltage

The potential of GND, PGND1, PGND2 pin must be minimum potential in all operating conditions.

3. Thermal design

Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4. Inter-pin shorts and mounting errors

Use caution when positioning the IC for mounting on printed circuit boards. The IC may be damaged if there is any connection error or if pins are shorted together.

5. Actions in strong electromagnetic field

Use caution when using the IC in the presence of a strong electromagnetic field as doing so may cause the IC to malfunction.

6 ASC

When using the IC, set the output transistor so that it does not exceed absolute maximum ratings or ASO.

7. Testing on application boards

When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process. Ground the IC during assembly steps as an antistatic measure. Use similar precaution when transporting or storing the IC.

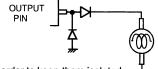
8. Electrical characteristics

The electrical characteristics in the Specifications may vary depending on ambient temperature, power supply voltage, circuit(s) externally applied, and/or other conditions. It is therefore requested to carefully check them including transient characteristics.

9. Not of a radiation-resistant design.

10. In the event that load containing a large inductance component

is connected to the output terminal, and generation of back-EMF at the start-up and when output is turned OFF is assumed, it is requested to insert a protection diode.



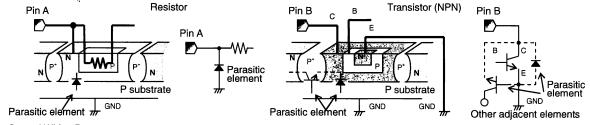
Regarding input pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of these P layers with the N layers of other elements, creating a parasitic diode or transistor. For example, the relation between each potential is as follows:

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode.

When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes can occur inevitable in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Accordingly, methods by which parasitic diodes operate, such as applying a voltage that is lower than the GND (P substrate) voltage to an input pin, should not be used.



12. Ground Wiring Pattern

When using both small signal and large current GND patterns, it is recommended to isolate the two ground patterns, placing a single ground point at the ground potential of application so that the pattern wiring resistance and voltage variations caused by large currents do not cause variations in the small signal ground voltage. Be careful not to change the GND wiring pattern of any external components, either.

13. Operating ranges

If it is within the operating ranges, certain circuit functions and operations are warranted in the working ambient temperature range. With respect to characteristic values, it is unable to warrant standard values of electric characteristics but there are no sudden variations in characteristic values within these ranges.

14. Thermal shutdown circuit

This IC is provided with a built-in thermal shutdown (TSD) circuit, which is activated when the chip temperature reaches the threshold value listed below. When TSD is on, the device goes to high impedance mode. Note that the TSD circuit is provided for the exclusive purpose shutting down the IC in the presence of extreme heat, and is not designed to protect the IC per se or guarantee performance when or after extreme heat conditions occur. Therefore, do not operate the IC with the expectation of continued use or subsequent operation once the TSD is activated.

TSD ON temperature [°C] (typ.)	Hysteresis temperature[°C] (typ.)
175	15

15. Heat sink (FIN)

Since the heat sink (FIN) is connected with the Sub, short it to the GND.

Notes

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Appendix1-Rev2.0